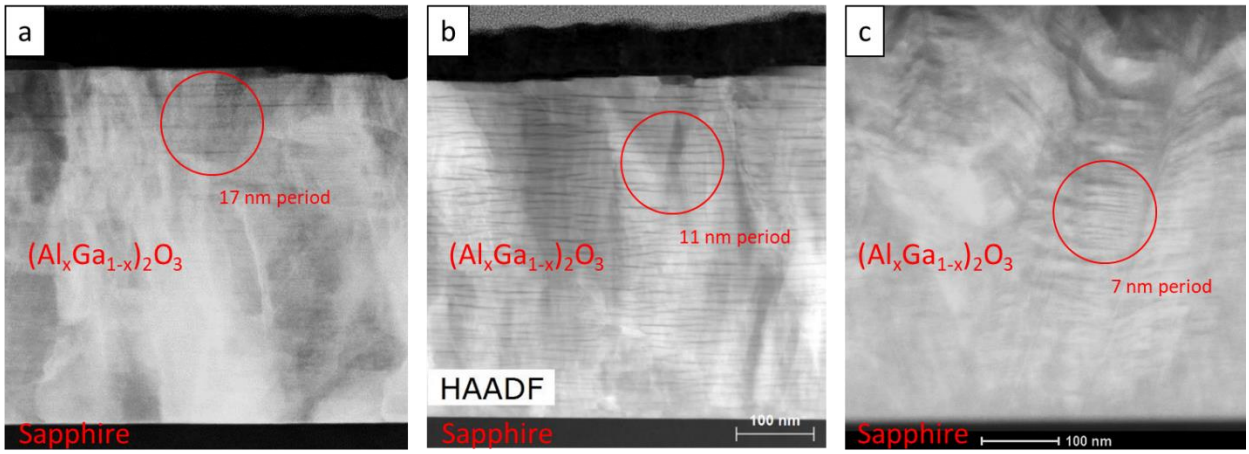

Figure 1. Dark field STEM images of $(Al_xGa_{1-x})_2O_3$ on sapphire showing Al rich striations for a) x = 0.04, b) x = 0.08, and c) x = 0.3 where higher Al content is correlated with decreased period spacing of the striations.

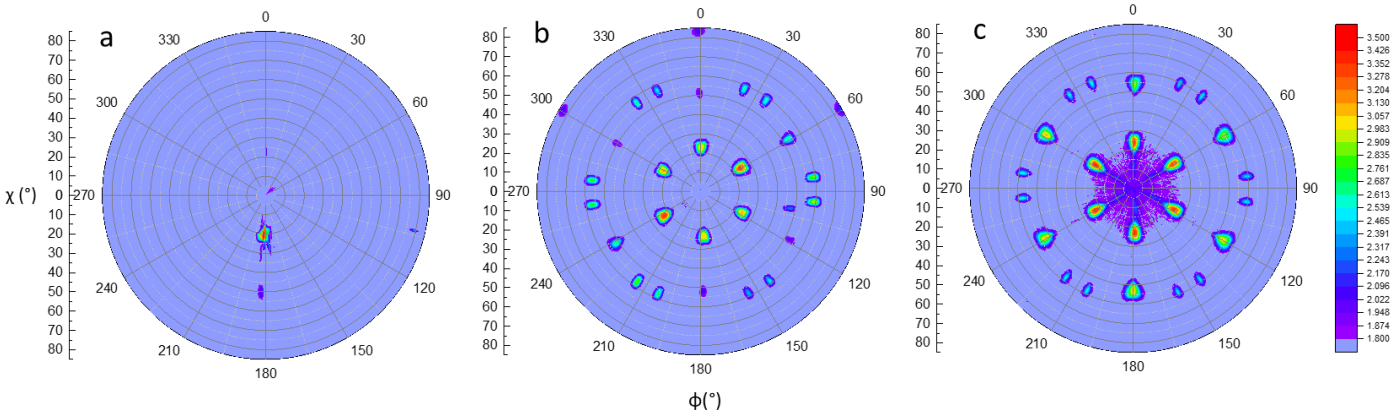

Figure 2. $(\bar{4}01)$ pole figures for (a) commercial $(\bar{2}01)$ β-Ga_2O_3 substrate; (b) $(\bar{2}01)$ Ga_2O_3 thin film grown on sapphire (c) $(\bar{2}01)$ $(Al_xGa_{1-x})_2O_3$ thin films (x=0.15) grown on sapphire